

1. Description

BLS60R036, the silicon N-channel Enhanced MOSFETs, is obtained by advanced Super Junction technology which reduce the conduction loss, improve switching performance. The transistor is suitable device for SMPS, high speed switching and general purpose applications.

KEY CHARACTERISTICS

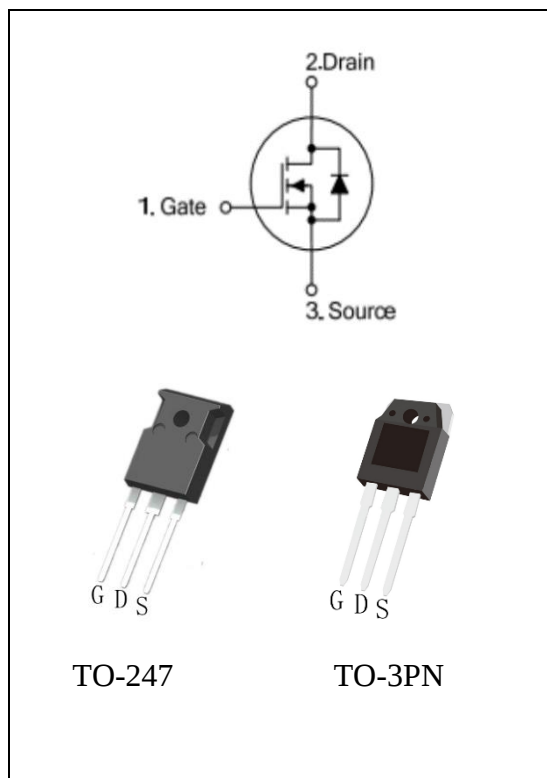
Parameter	Value	Unit
$V_{DS@Tj.max}$	650	V
I_D	75	A
$R_{DS(ON).Typ}$	0.032	Ω

FEATURES

- Fast Switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- High frequency switching mode power supply



ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
BLS60R036-F	TO-247	S60R036	Tube
BLS60R036-W	TO-3PN	S60R036	Tube

BLS60R036-F (2) Package type (1) Chip name (1) BLS60R036:600V 36mΩ (2) F:TO-247 W:TO-3PN	 XXXX YYWW ZZ SSSSS XXXX: Product Code YYWW: Year&Week ZZ: Assembly Code SSSSS: Lot Code
---	--

2. ABSOLUTE RATINGS

 at $T_C = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	75	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	48	A
I_{DM}	Pulsed Drain Current(Note1)	300	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy(Note2)	2200	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	15	V/ns
P_D	Power Dissipation	480	W
	Derating Factor above 25°C	4.2	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

3. Thermal characteristics

Thermal characteristics

Symbol	Parameter	RATINGS	Units
$R_{\theta JC}$	Junction-to-Case	0.24	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient	62.0	$^\circ\text{C}/\text{W}$

4. Electrical Characteristics

 at $T_C = 25^\circ\text{C}$, unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	600	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu\text{A}$, Reference 25°C	--	0.58	--	V/ $^\circ\text{C}$

I _{DSS}	Drain to Source Leakage Current	V _{DS} = 600V, V _{GS} = 0V, T _j = 25°C	--	--	1	μA
		V _{DS} = 480V, V _{GS} = 0V, T _j = 125°C	--	--	100	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} = +30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} = -30V	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} = 10V, I _D = 35A (Note4)	--	0.032	0.036	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA (Note4)	3.5	4.0	4.5	V

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R _g	Gate resistance	f = 1.0MHz	--	0.98	--	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	7900	--	PF
C _{oss}	Output Capacitance		--	9200	--	
C _{rss}	Reverse Transfer Capacitance		--	900	--	

Switching Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D = 45A V _{DD} = 400V V _{GS} = 13V R _G = 1.8Ω	--	30	--	ns
t _r	Rise Time		--	28	--	
t _{d(OFF)}	Turn-Off Delay Time		--	90	--	
t _f	Fall Time		--	6	--	
Q _g	Total Gate Charge	I _D = 70A V _{DD} = 480V V _{GS} = 10V	--	160	--	nC
Q _{gs}	Gate to Source Charge		--	46.5	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	57	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)	TC=25 °C	--	--	75	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	225	A
V _{SD}	Diode Forward Voltage	IS=75A, VGS=0V(Note4)	--	--	1.2	V
T _{rr}	Reverse Recovery Time	IS=45A, Tj = 25°C dIF/dt=100A/us, VGS=0V	--	620	--	ns
Q _{rr}	Reverse Recovery Charge		--	11000	--	nC

Note1: Pulse width limited by maximum junction temperature

Note2: L=10mH, VDs=50V, Start TJ=25°C

Note3: ISD =75A, di/dt ≤100A/us, VDD≤BVDS, Start TJ=25°C

Note4: Pulse width tp≤300μs, δ≤2%

5. Characteristics Curves

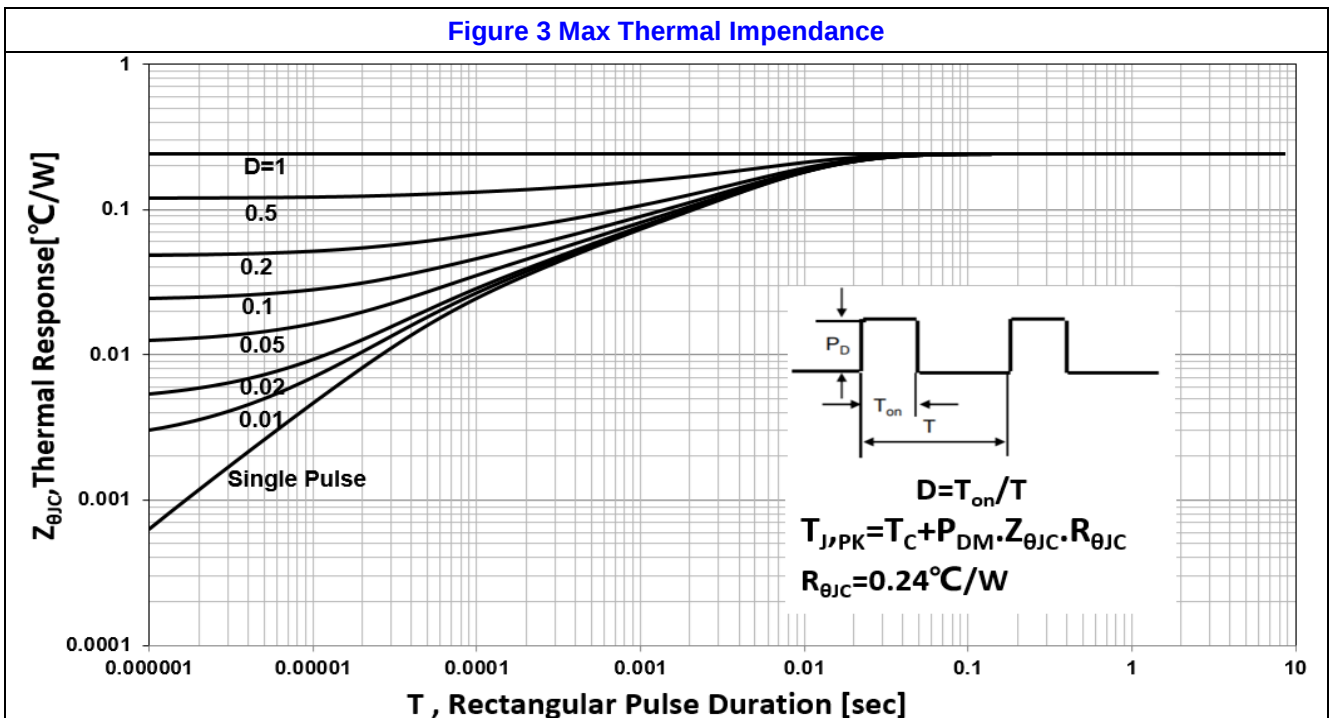
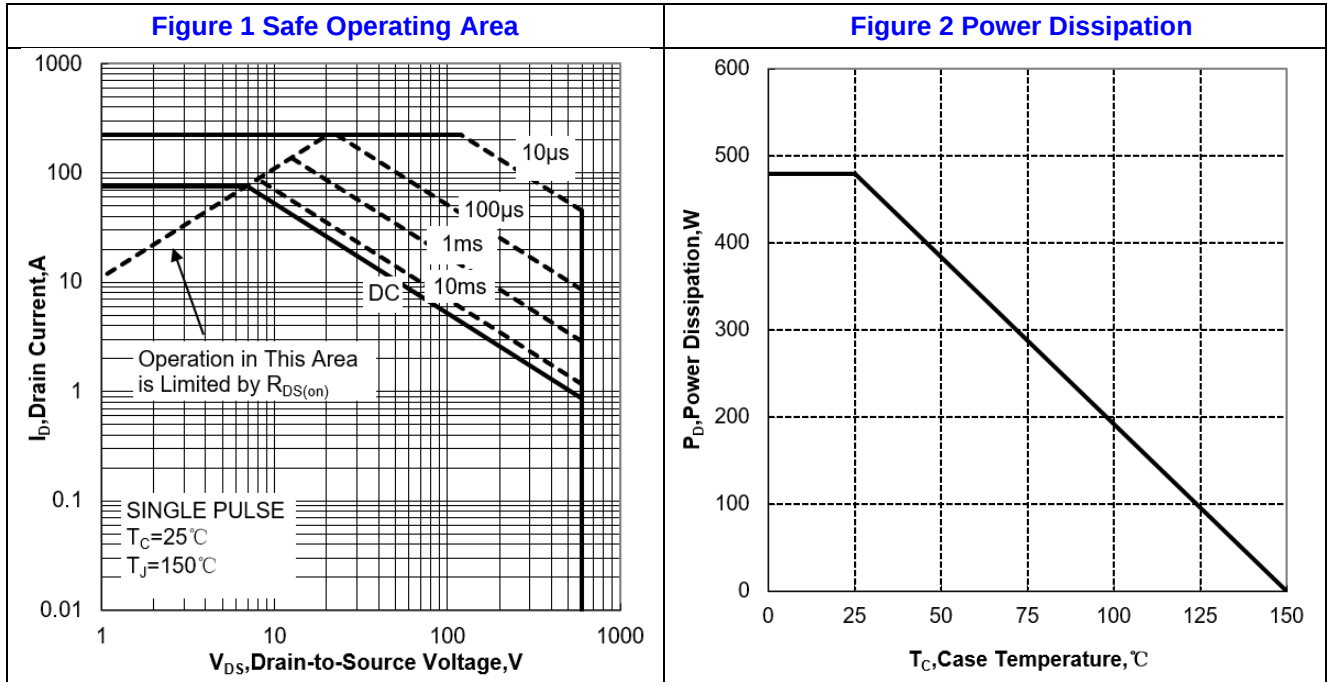


Figure 4 Typical Output Characteristics

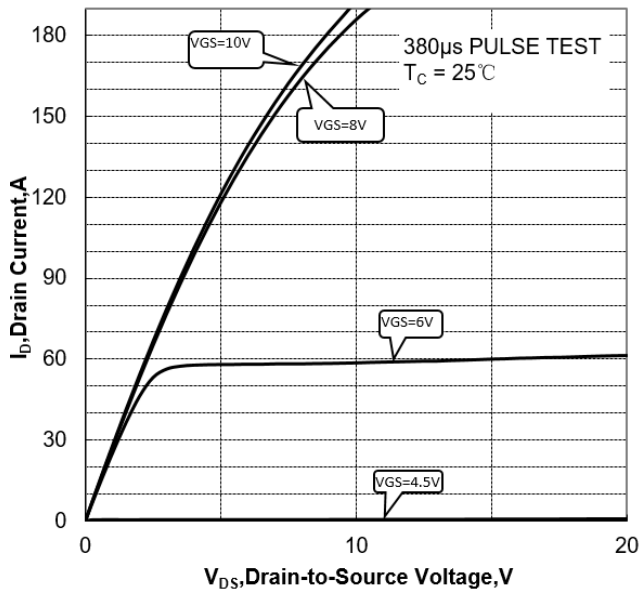


Figure 5 Typical Transfer Characteristics

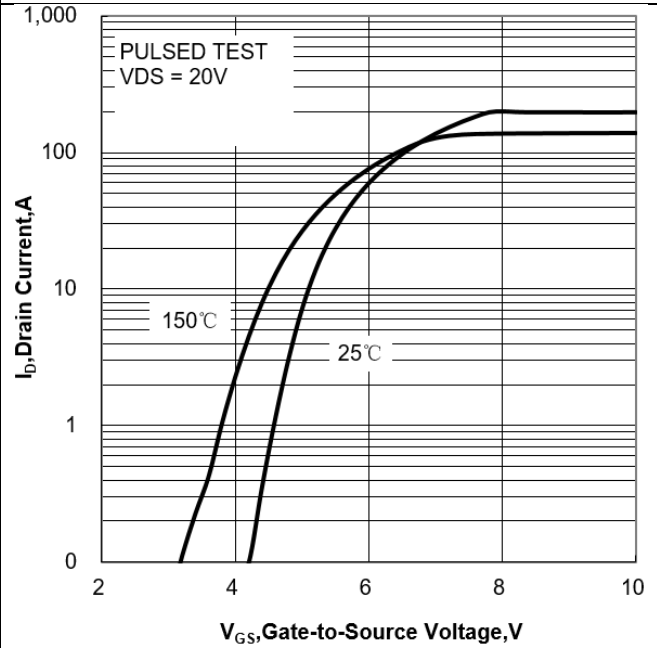


Figure 6 Typical Drain to Source ON Resistance vs Drain Current

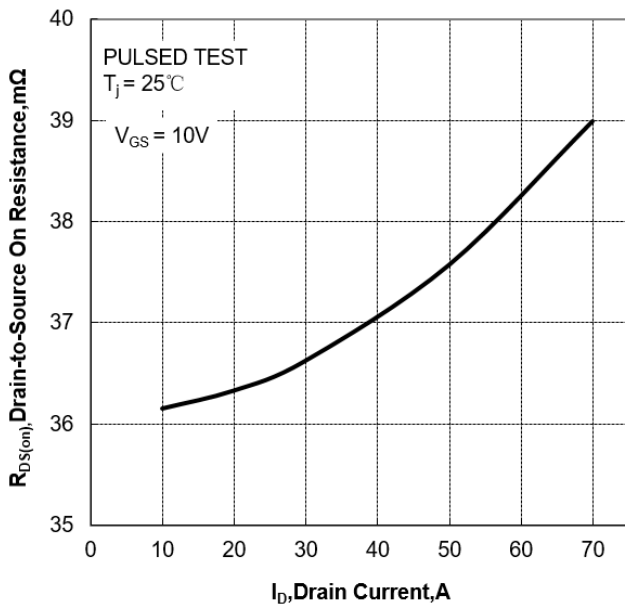


Figure 7 Typical Drain to Source on Resistance vs Junction Temperature

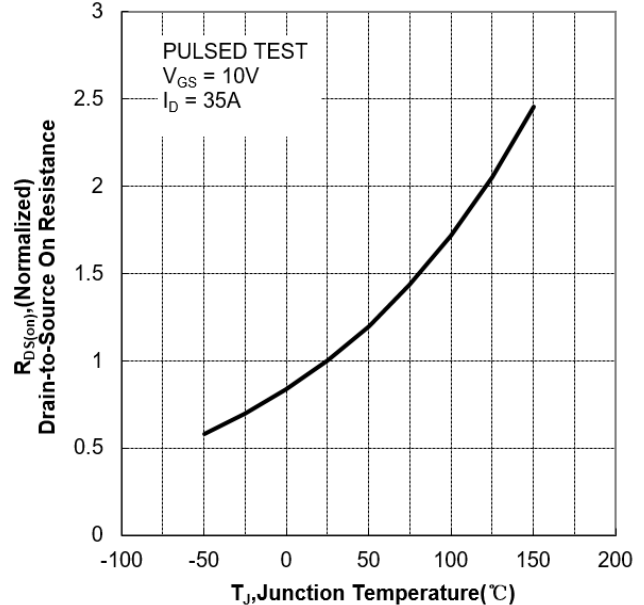


Figure 8 Typical Theshold Voltage vs Junction Temperature

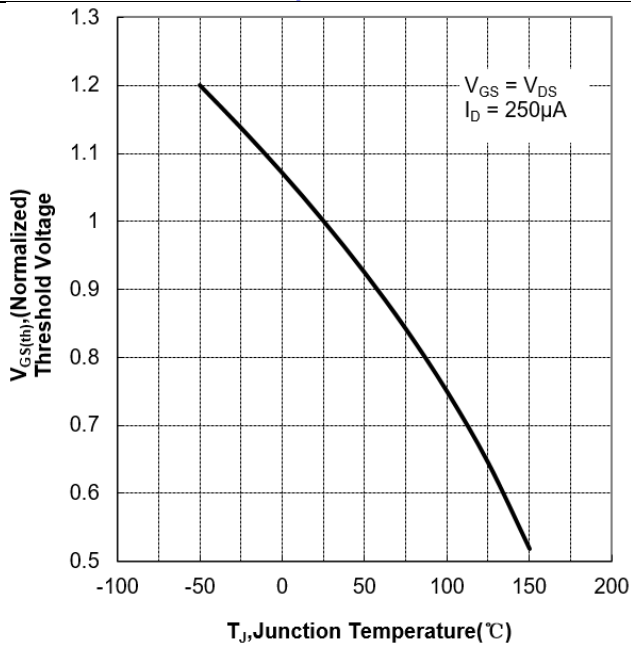


Figure 9 Typical Breakdown Voltage vs Junction Temperature

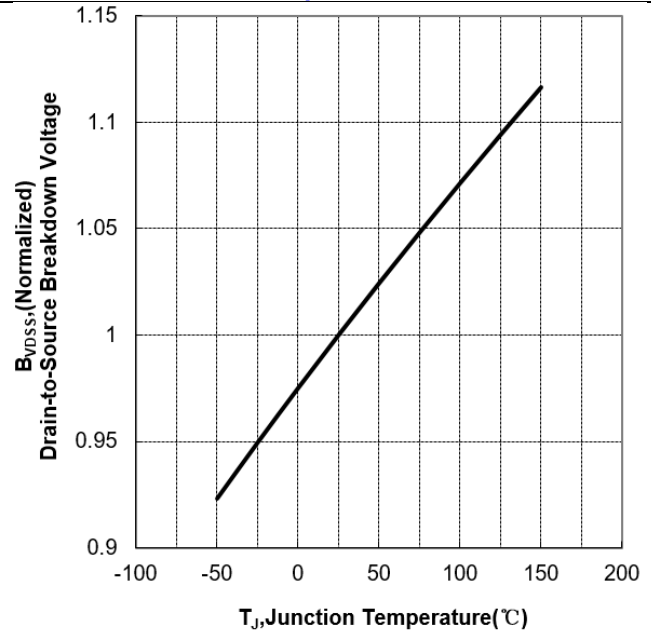


Figure 10 Typical Capacitance vs Drain to Source Voltage

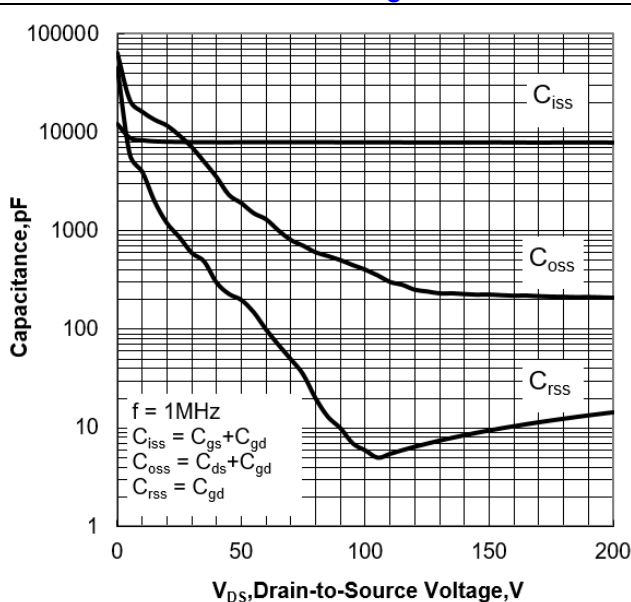
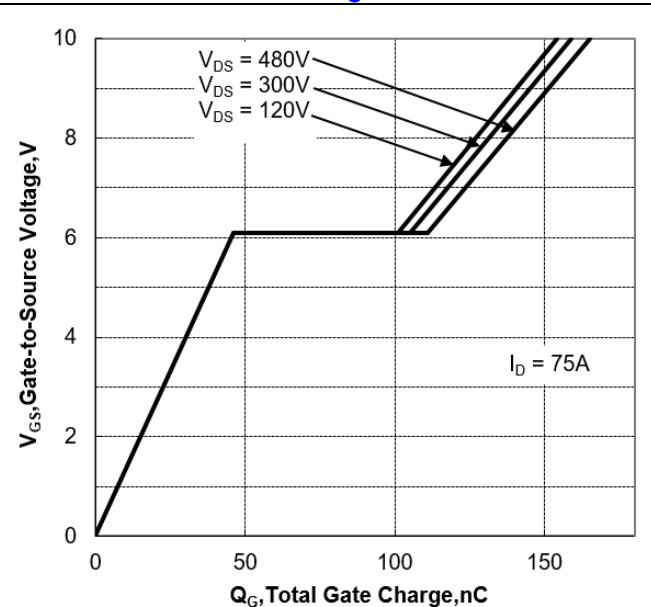


Figure 11 Typical Gate Charge vs Gate to Source Voltage



6. Test Circuit and Waveform

Figure 12 Gate Charge Test Circuit

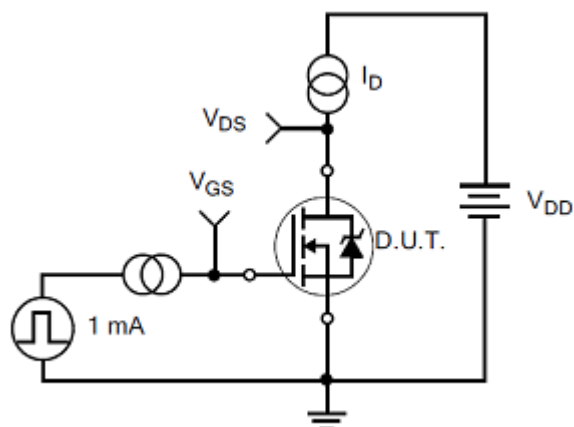


Figure 13 Gate Charge Waveforms

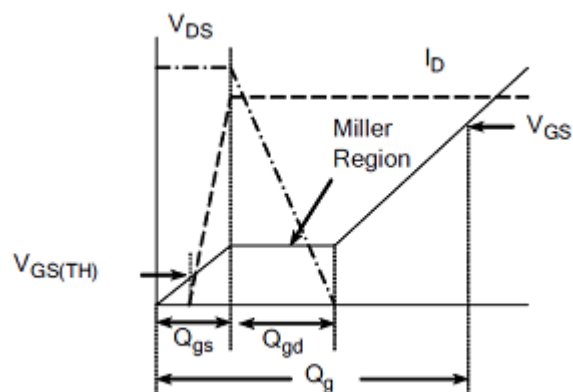


Figure 14 Resistive Switching Test Circuit

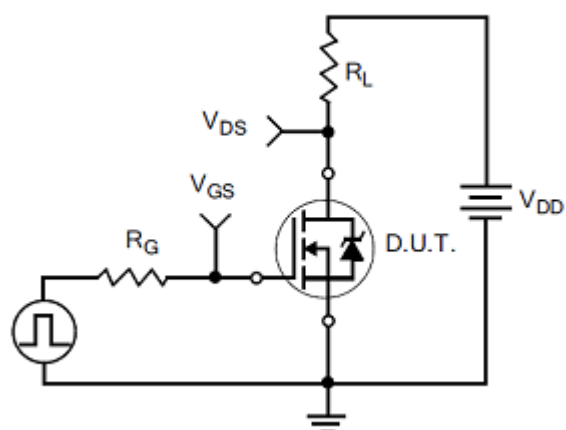


Figure 15 Resistive Switching Waveforms

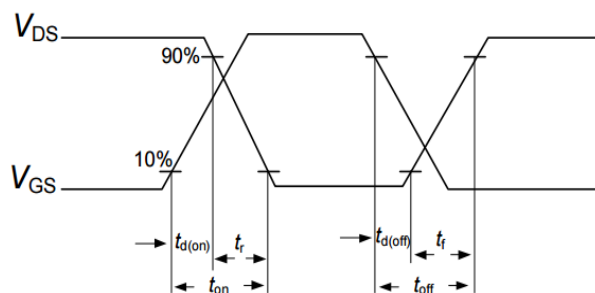


Figure 16 Diode Reverse Recovery Test Circuit

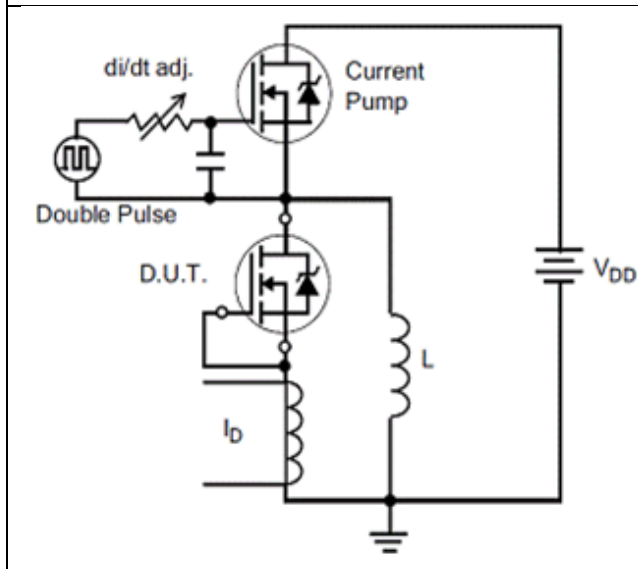


Figure 17 Diode Reverse Recovery Waveform

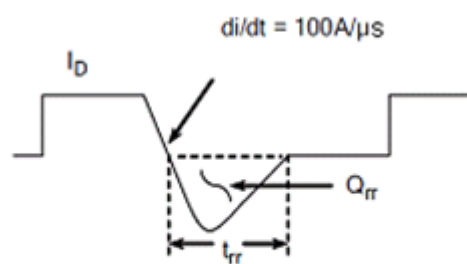


Figure 18 Unclamped Inductive Switching Test Circuit

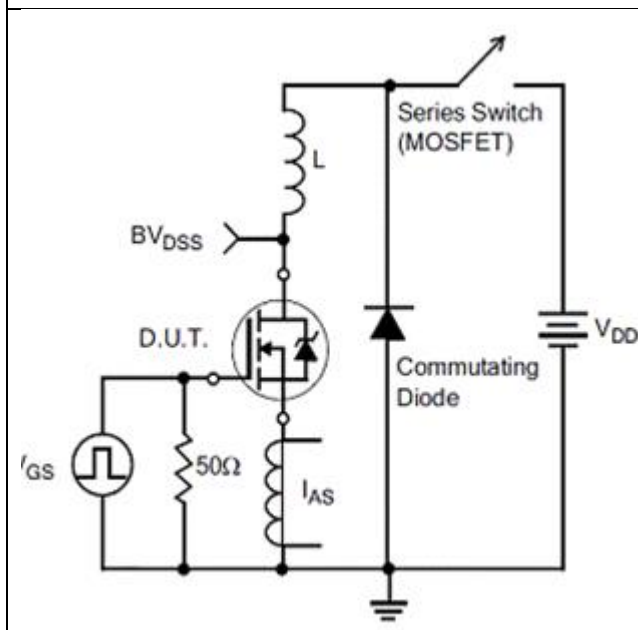
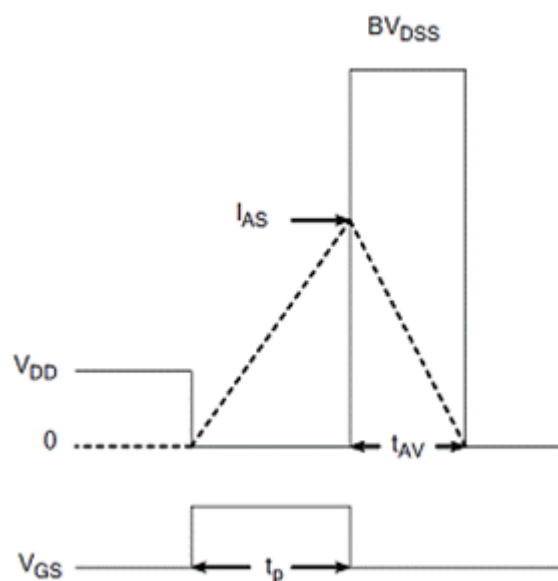
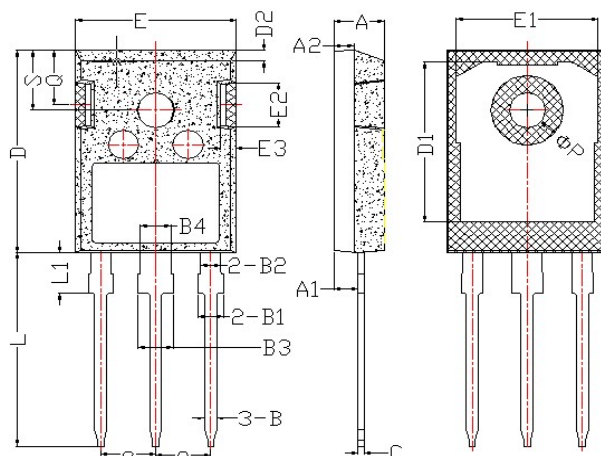


Figure 19 Unclamped Inductive Switching Waveform

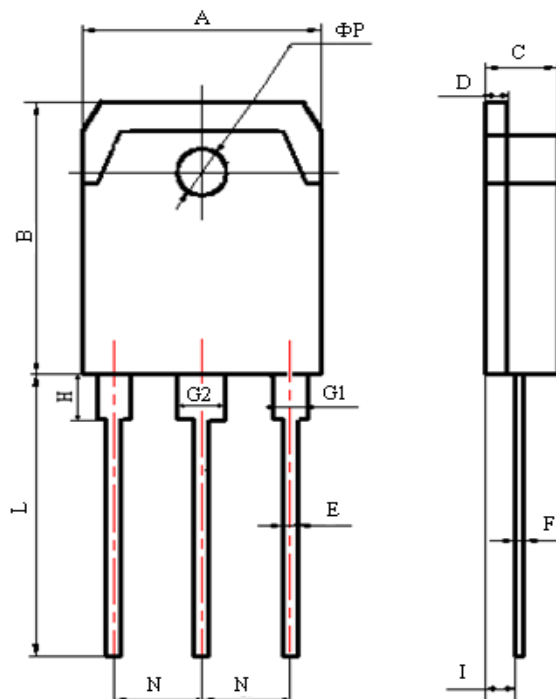


7. Package Description



Items	Values(mm)	
	MIN	MAX
A	4.6	5.2
A1	2.2	2.6
B	0.9	1.4
B1	1.75	2.35
B2	1.75	2.15
B3	2.8	3.35
B4	2.8	3.15
C	0.5	0.7
D	20.60	21.30
D1	16	18
E	15.5	16.10
E1	13	14.7
E2	3.80	5.3
E3	0.8	2.60
e	5.2	5.7
L	19	20.5
L1	3.9	4.6
Φ_P	2.5	3.70
Q	5.2	6.00
S	5.8	6.6

TO-247 Package



Items	Values(mm)	
	MIN	MAX
A	15.00	16.00
B	19.20	20.60
C	4.60	5.00
D	1.40	1.60
E	0.90	1.10
F	0.50	0.70
G1	2.00	2.20
G2	3.00	3.20
H	3.00	3.70
I	1.20	1.70
	2.70	2.90
L	19.00	21.00
N	5.25	5.65
Φ P	3.10	3.30

TO-3PN Package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shanghai Belling reserves the right to make changes in this specification sheet and is subject to change without prior notice.

CONTACT:**上海贝岭股份有限公司（总部）**

地址：上海市宜山路 810 号

邮编：200233

电话：021-24261000

产品业务咨询及技术支持

电话：021-24261326

传真：021-64852222

邮箱：marketing@belling.com.cn

上海贝岭深圳分公司（华南区）

地址：深圳市福田区中心区民田路新华保险大厦 1510 室

邮编：518031

电话：0755-33336776 0755-33336770

传真：0755-33336788

上海贝岭北京办事处（华北区）

地址：北京市西城区新华里 16 号院锦官苑小区 10 号楼 1 单元 1505 室

邮编：100044

电话：010-64179374

传真：010-8835 9236